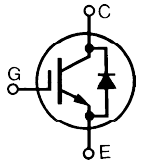
IXYS

Not for New Design

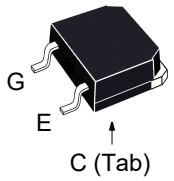
High Voltage, High Gain BIMOSFET™ Monolithic Bipolar MOS Transistor

IXBT20N300HV

V_{CES} = 3000V
I_{C110} = 20A
$V_{CE(sat)} \leq$ 3.2V



TO-268HV



G = Gate C = Collector
E = Emiiter Tab = Collector

Symbol	Test Conditions	Maximum Ratings	
V_{CES}	T_C = 25°C to 150°C	3000	V
V_{CGR}	T_J = 25°C to 150°C, R_{GE} = 1MΩ	3000	V
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	T_C = 25°C	50	A
I_{C110}	T_C = 110°C	20	A
I_{CM}	T_C = 25°C, 1ms	140	A
SSOA (RBSOA)	V_{GE} = 15V, T_{VJ} = 125°C, R_G = 20Ω	I_{CM} = 130	A
	Clamped Inductive Load	1500	V
P_C	T_C = 25°C	250	W
T_J		-55 ... +150	°C
T_{JM}		150	°C
T_{stg}		-55 ... +150	°C
T_{SOLD}	Plastic Body for 10s	260	°C
Weight		4	g

Symbol	Test Conditions (T_J = 25°C Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max.	
BV_{CES}	I_C = 250μA, V_{GE} = 0V	3000			V
$V_{GE(th)}$	I_C = 250μA, V_{CE} = V_{GE}	2.5		5.0	V
I_{CES}	V_{CE} = 0.8 • V_{CES}, V_{GE} = 0V			35	μA
	T_J = 125°C			1.5	mA
I_{GES}	V_{CE} = 0V, V_{GE} = ± 20V			±100	nA
$V_{CE(sat)}$	I_C = 20A, V_{GE} = 15V, Note 1		2.7	3.2	V
	T_J = 125°C		3.2		V

Features

- High Voltage Package
- High Blocking Voltage
- Anti-Parallel Diode
- Low Conduction Losses

Advantages

- Low Gate Drive Requirement
- High Power Density

Applications:

- Switch-Mode and Resonant-Mode Power Supplies
- Uninterruptible Power Supplies (UPS)
- Laser Generators
- Capacitor Discharge Circuits
- AC Switches

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Symbol	Test Conditions (T_J = 25°C Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max.	
g_{fs}	I_C = 20A, V_{CE} = 10V, Note 1	11	18		S
C_{ies}	V_{CE} = 25V, V_{GE} = 0V, f = 1MHz		2230		pF
C_{oes}			92		pF
C_{res}			33		pF
Q_g	I_C = 20A, V_{GE} = 15V, V_{CE} = 1000V		105		nC
Q_{ge}			13		nC
Q_{gc}			45		nC
$t_{d(on)}$	**Resistive Switching Times, T_J = 25°C**		64		ns
t_r	I_C = 20A, V_{GE} = 15V		210		ns
$t_{d(off)}$	V_{CE} = 1250V, R_G = 10Ω		300		ns
t_f			504		ns
$t_{d(on)}$	**Resistive Switching Times, T_J = 125°C**		68		ns
t_r	I_C = 20A, V_{GE} = 15V		540		ns
$t_{d(off)}$	V_{CE} = 1250V, R_G = 10Ω		300		ns
t_f			395		ns
R_{thJC}				0.50	°C/W

Reverse Diode

Symbol	Test Conditions (T_J = 25°C Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max.	
V_F	I_F = 20A, V_{GE} = 0V			2.1	V
t_{rr}	I_F = 10A, V_{GE} = 0V, -di_F/dt = 100A/μs		1.35		μs
I_{RM}	V_R = 100V, V_{GE} = 0V		30		A

Note 1: Pulse test, t ≤ 300μs, duty cycle, d ≤ 2%.

Littelfuse reserves the right to change limits, test conditions and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents: 4,835,592 4,860,072 4,881,106 4,931,844 5,017,508 5,034,796 5,049,961 5,063,307 5,187,117 5,237,481 5,381,025 5,486,715 6,162,665 6,259,123 B1 6,306,728 B1 6,404,065 B1 6,534,343 6,583,505 6,683,344 6,710,405 B2 6,710,463 6,727,585 6,759,692 6,771,478 B2 7,005,734 B2 7,063,975 B2 7,071,537 7,157,338B2

Fig. 1. Output Characteristics @ T_J = 25ºC

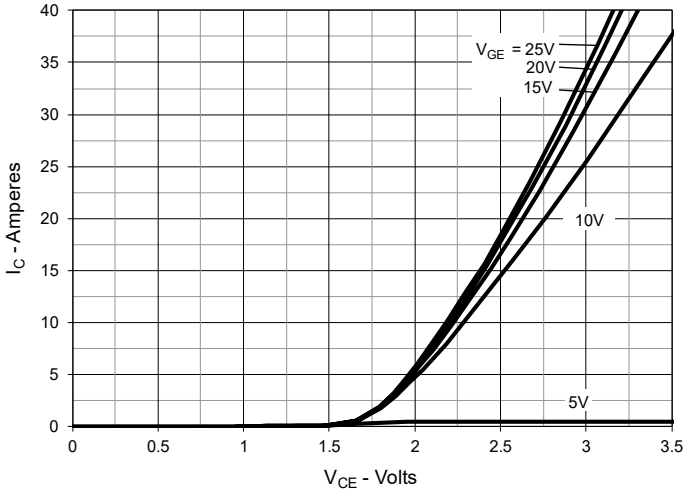


Fig. 2. Extended Output Characteristics @ T_J = 25ºC

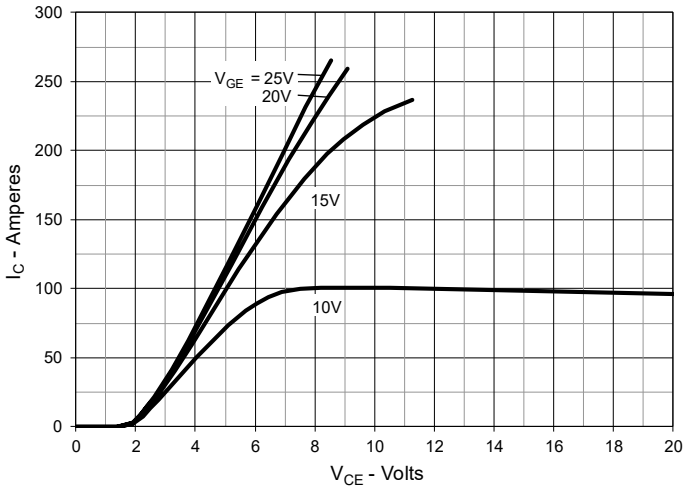


Fig. 3. Output Characteristics @ T_J = 125ºC

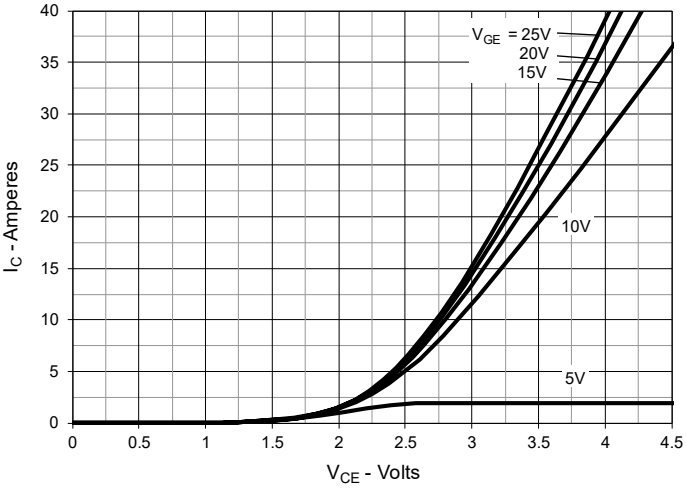


Fig. 4. Dependence of $V_{CE(sat)}$ on Junction Temperature

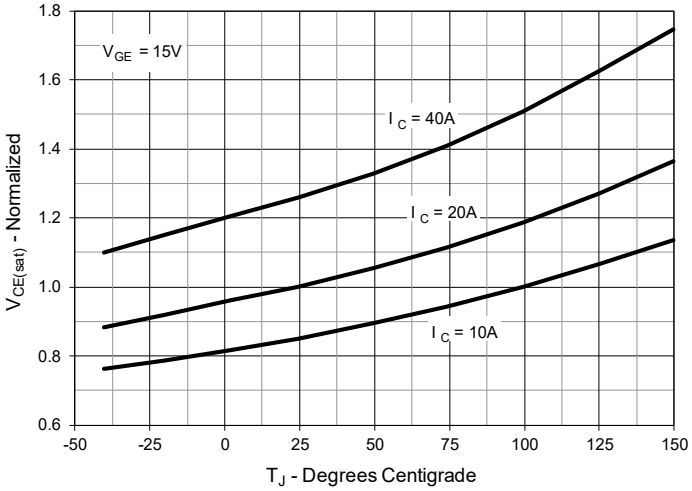


Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter Voltage

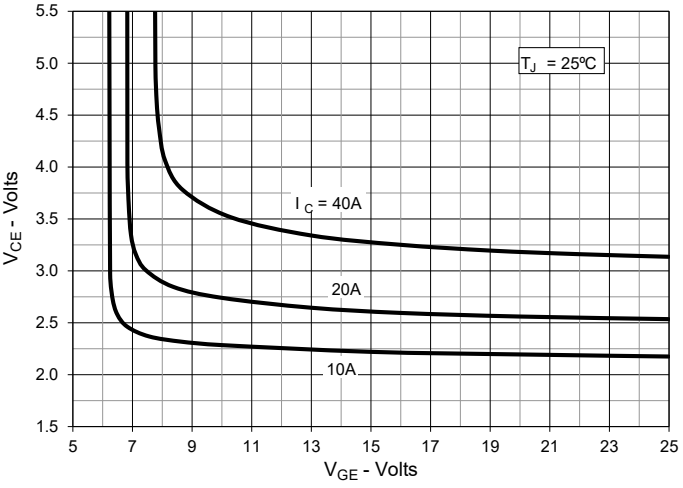
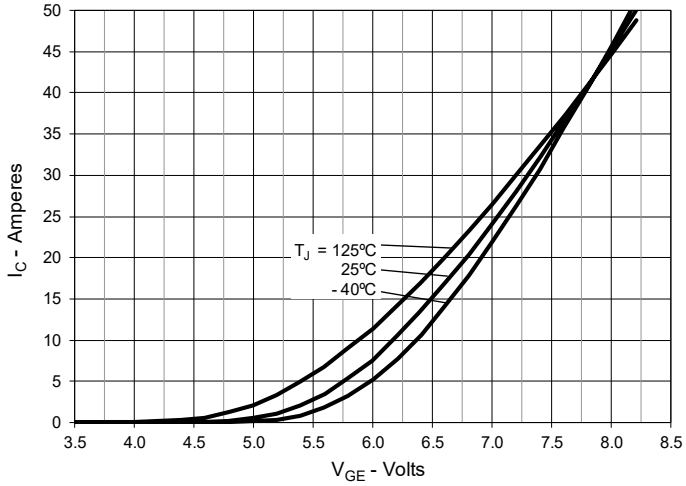


Fig. 6. Input Admittance



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Fig. 7. Transconductance

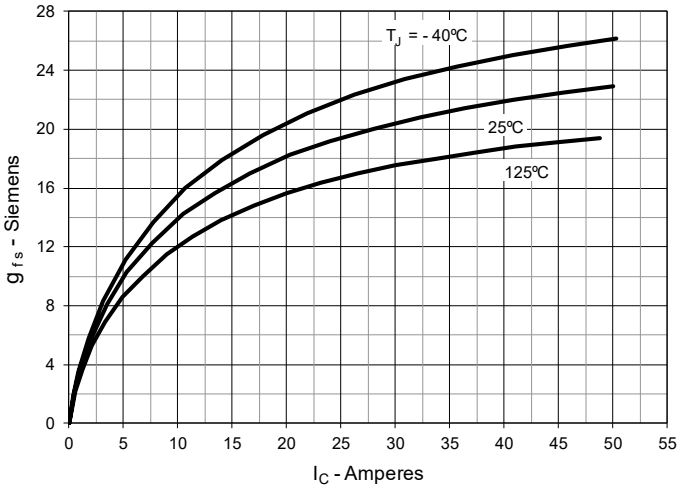


Fig. 8. Forward Voltage Drop of Intrinsic Diode

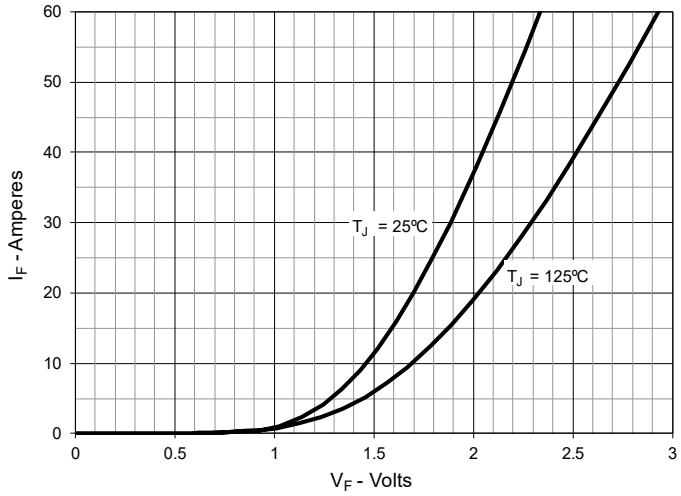


Fig. 9. Gate Charge

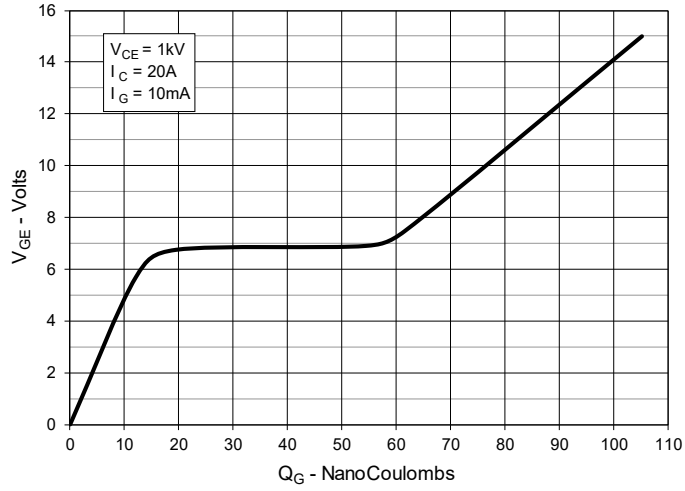


Fig. 10. Capacitance

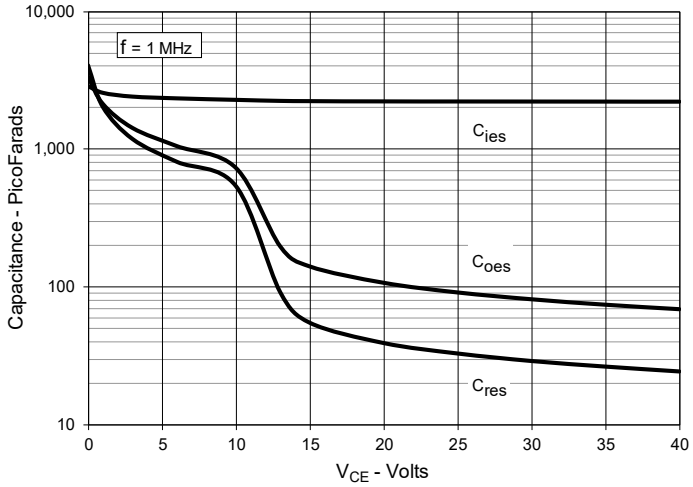


Fig. 11. Reverse-Bias Safe Operating Area

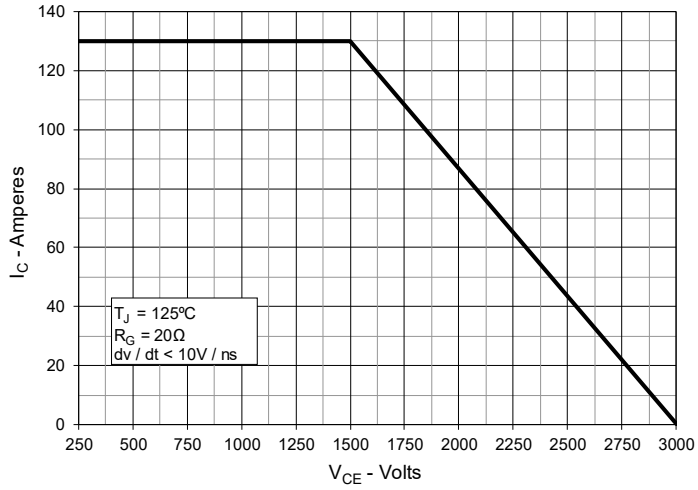
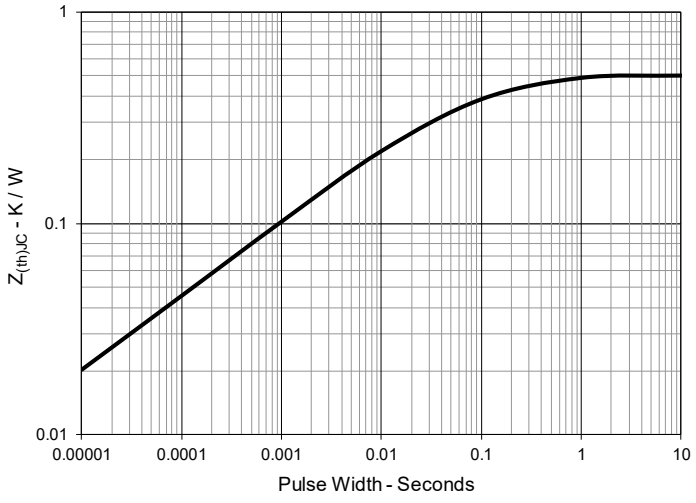


Fig. 12. Maximum Transient Thermal Impedance



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Fig. 13. Resistive Turn-on Rise Time vs. Junction Temperature

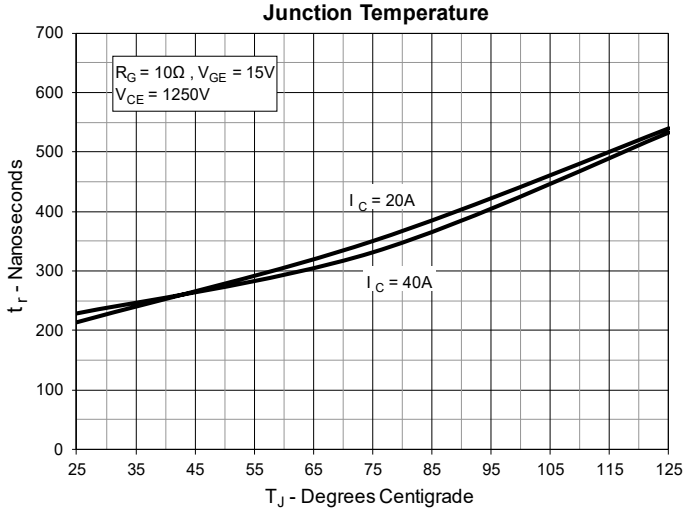


Fig. 14. Resistive Turn-on Rise Time vs. Collector Current

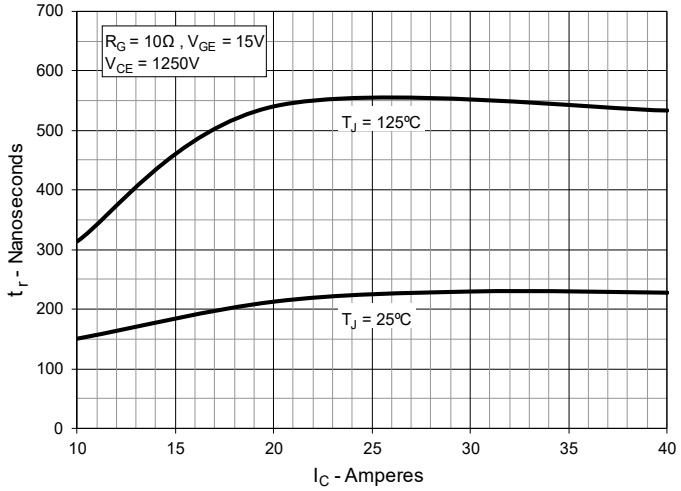


Fig. 15. Resistive Turn-on Switching Times vs. Gate Resistance

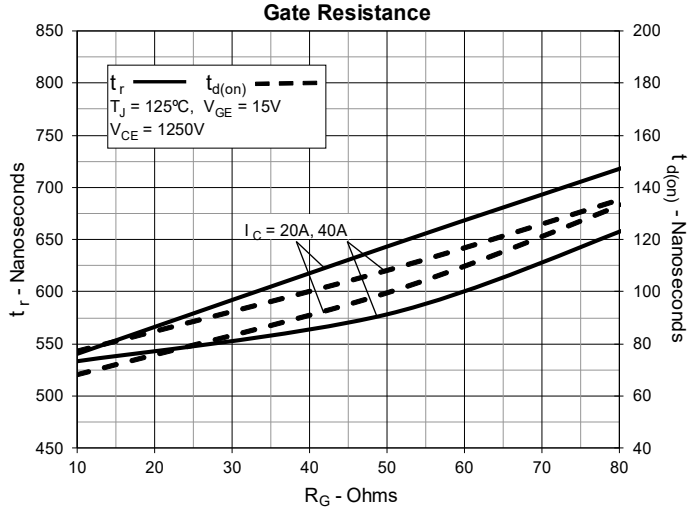


Fig. 16. Resistive Turn-off Switching Times vs. Junction Temperature

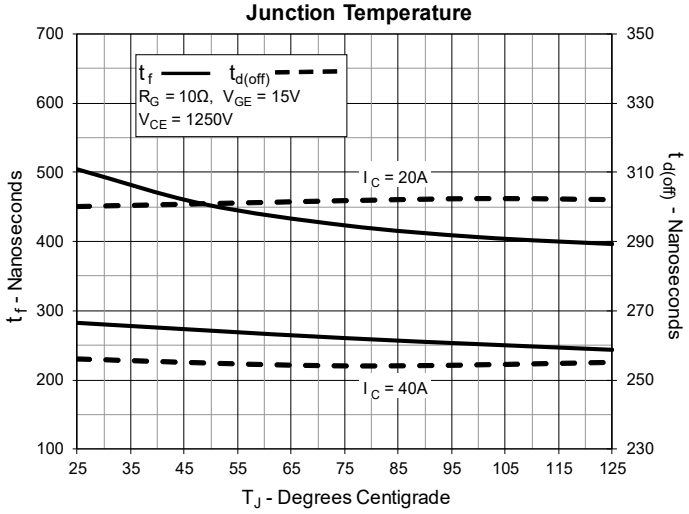


Fig. 17. Resistive Turn-off Switching Times vs. Collector Current

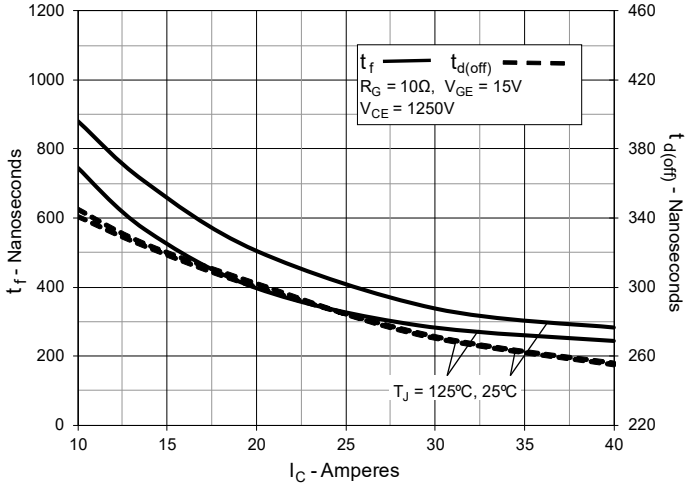
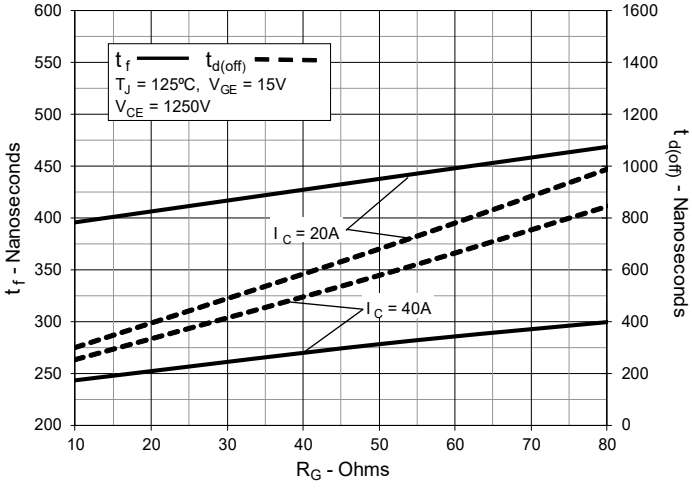
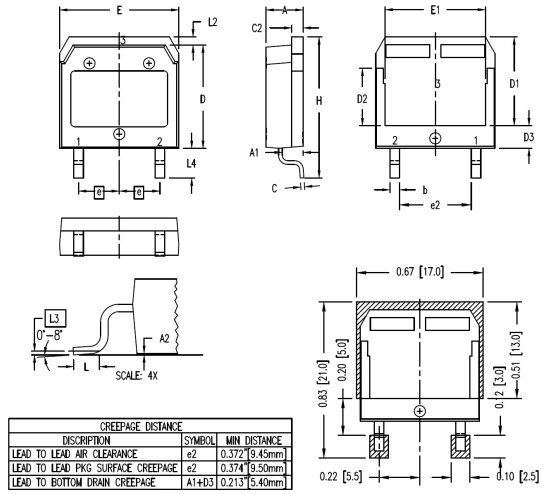


Fig. 18. Resistive Turn-off Switching Times vs. Gate Resistance



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TO-268HV Outline



CREEPAGE DISTANCE			
DISCRIPTION	SYMBOL	MIN DISTANCE	
LEAD TO LEAD AIR CLEARANCE	e2	0.372"	[9.45mm]
LEAD TO LEAD PKG SURFACE CREEPAGE	e2	0.374"	[9.50mm]
LEAD TO BOTTOM DRAIN CREEPAGE	A1+D3	0.213"	[5.40mm]

1 - Gate
2 - Emitter
3 - Collector

SYM	INCHES		MILLIMETER	
	MIN	MAX	MIN	MAX
A	.193	.201	4.90	5.10
A1	.106	.114	2.70	2.90
A2	.001	.010	0.02	0.25
b	.045	.057	1.15	1.45
C	.016	.026	0.40	0.65
C2	.057	.063	1.45	1.60
D	.543	.551	13.80	14.00
D1	.465	.476	11.80	12.10
D2	.295	.307	7.50	7.80
D3	.114	.126	2.90	3.20
E	.624	.632	15.85	16.05
E1	.524	.535	13.30	13.60
e	.215 BSC		5.45 BSC	
(e2)	.374	.386	9.50	9.80
H	.736	.752	18.70	19.10
L	.067	.079	1.70	2.00
L2	.039	.045	1.00	1.15
L3	.010 BSC		0.25 BSC	
L4	.150	.161	3.80	4.10

IXYS
A Littelfuse Technology

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